

# **N-Channel Power MOSFET**

900V, 4A, 4.0Ω

#### **FEATURES**

- Low R<sub>DS(ON)</sub> 4Ω (Max.)
- Low gate charge typical @ 25nC (Typ.)
- Improve dV/dt capability

KEY PERFORMANCE PARAMETERS				
PARAMETER	RAMETER VALUE UNIT			
$V_{DS}$	900	V		
R <sub>DS(on)</sub> (max)	4	Ω		
$Q_g$	25	nC		

#### **APPLICATION**

High efficiency switch mode power Supply

• Lighting





Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> =25°C unless otherwise noted)					
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT	
Drain-Source Voltage	$V_{DS}$	900 \		V	
Gate-Source Voltage	$V_{GS}$	±30 V		V	
Continuous Drain Current (Note 4) T <sub>C</sub> = 25°C	I <sub>D</sub>	4	4*	۸	
T <sub>C</sub> = 100°C		2.2	2.2*	Α	
Pulsed Drain Current (Note 2)	I <sub>DM</sub>	16	16 *	Α	
Total Power Dissipation @ T <sub>C</sub> = 25°C	P <sub>DTOT</sub>	123	38.7	W	
Single Pulsed Avalanche Energy (Note 3)	E <sub>AS</sub>	474		mJ	
Single Pulsed Avalanche Current (Note 3)	I <sub>AS</sub>	4		Α	
Repetitive Avalanche Energy <sup>(Note 2)</sup>	E <sub>AR</sub>	12.3		mJ	
Peak Diode Recovery (Note 7)	dV/dt	4.	.5	V	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to	+150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT
Junction to Case Thermal Resistance	R <sub>eJC</sub>	1.01	3.23	°C/W
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>	62.5		°C/W

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air.



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	900			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2		4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 900V, V_{GS} = 0V$	I <sub>DSS</sub>		-	10	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.0A$	R <sub>DS(on)</sub>		3.2	4.0	Ω
Forward Transconductance	$V_{DS} = 30V, I_{D} = 2.0A$	<b>g</b> fs		6		S
Dynamic (Note 5)				0		
Total Gate Charge	7001/ 1 4 04	$Q_g$		25		
Gate-Source Charge	$V_{DS} = 720V, I_D = 4.0A,$	$Q_{gs}$	(	4.8		nC
Gate-Drain Charge	V <sub>GS</sub> = 10V	$Q_{gd}$		10.2		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>iss</sub>		955		
Output Capacitance	f = 1.0MHz	Coss		80		pF
Gate Resistance	F = 1MHz, open drain	$R_g$		-	4	Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 450V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 4.0A, V_{GS} = 10V,$	t <sub>d(on)</sub>		49		
Turn-On Rise Time		t <sub>r</sub>		38		]
Turn-Off Delay Time		t <sub>d(off)</sub>		146		ns
Turn-Off Fall Time		t <sub>f</sub>		50		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_S = 4.0A$ , $V_{GS} = 0V$	V <sub>SD</sub>		-	1.5	V
Reverse Recovery Time	$V_{GS} = 0V, I_{S} = 4A$	t <sub>rr</sub>		487		ns
Reverse Recovery Charge	$d\hat{I}_F/dt = 100A/\mu s$	Q <sub>rr</sub>		2.8		μC

#### Notes:

- Current limited by package.
- Pulse width limited by the maximum junction temperature.
- 3. L = 56mH,  $I_{AS}$  = 4.0A,  $V_{DD}$  = 50V,  $R_{G}$  = 25 $\Omega$ , Starting  $T_{J}$  = 25 $^{\circ}$ C.
- 4. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.
- 7.  $I_{SD} \le 4A$ ,  $dI/dt \le 200A/uS$ ,  $V_{DD} \le BV_{DSS}$ , Starting  $T_J = 25^{\circ}C$ .



### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM4N90CZ C0G	TO-220	50pcs / Tube
TSM4N90CI C0G	ITO-220	50pcs / Tube

#### Note:

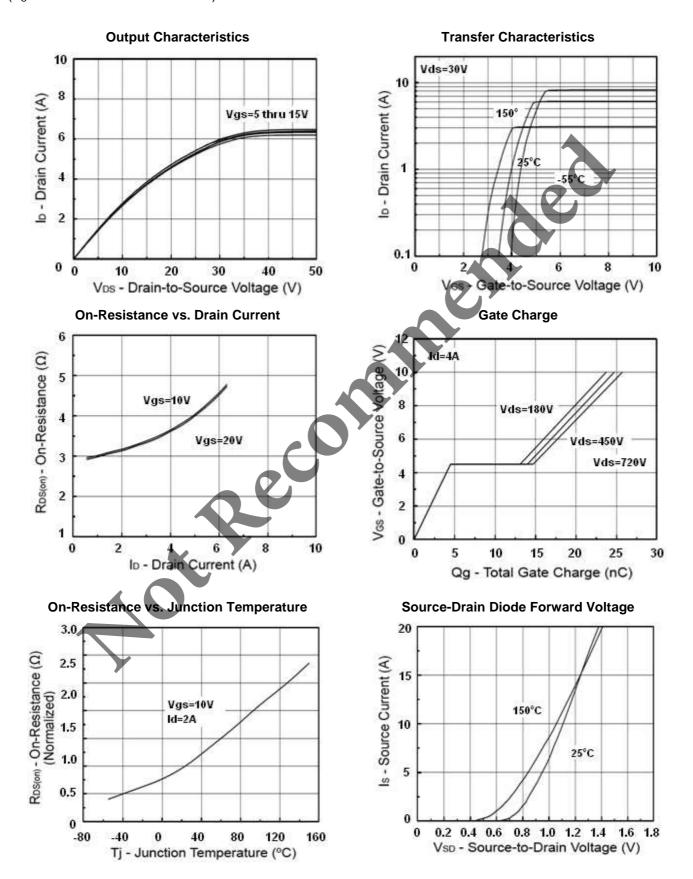
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition





## **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

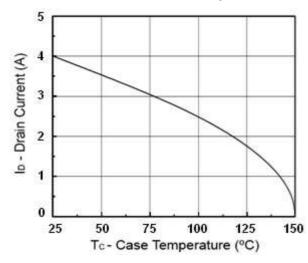




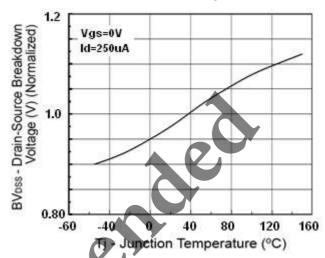
## **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

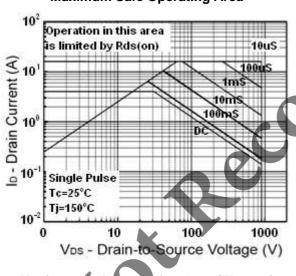




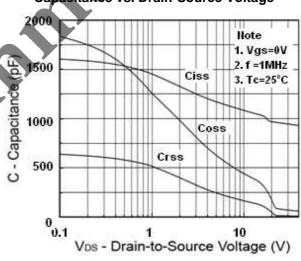
BV<sub>DSS</sub> vs. Junction Temperature



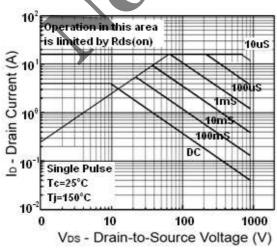
**Maximum Safe Operating Area** 



Capacitance vs. Drain-Source Voltage



Maximum Safe Operating Area (ITO-220)

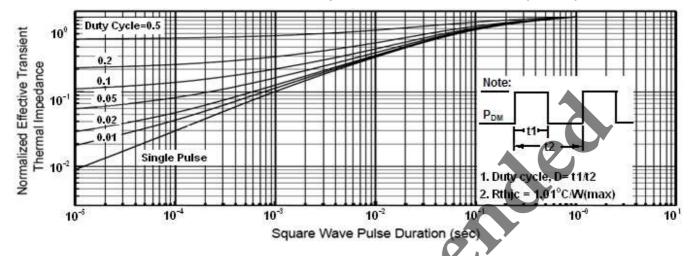




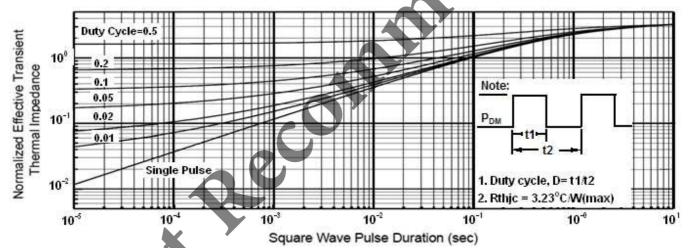
### **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

### Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-220)

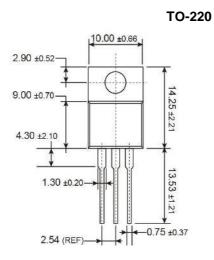


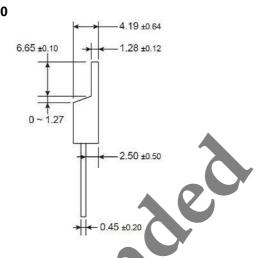
# Normalized Thermal Transient Impedance, Junction-to-Ambient (ITO-220)





# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





## **MARKING DIAGRAM**



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb **Q** =Mar =Apr

S =May T =Jun

W =Sep X =Oct



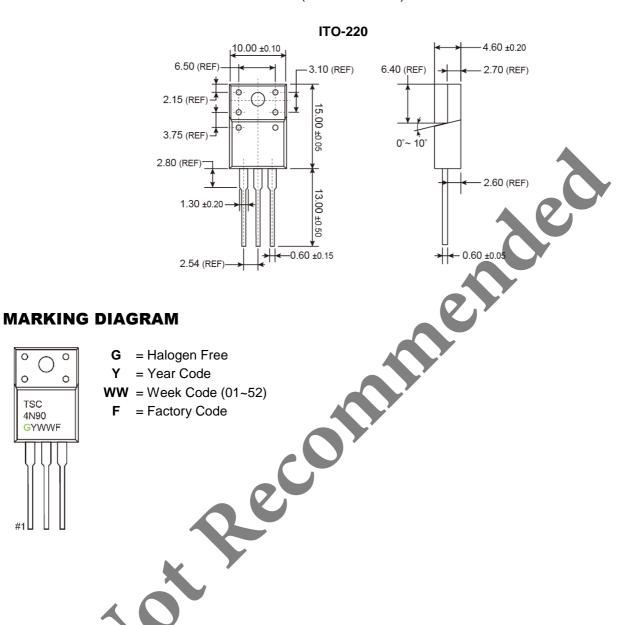
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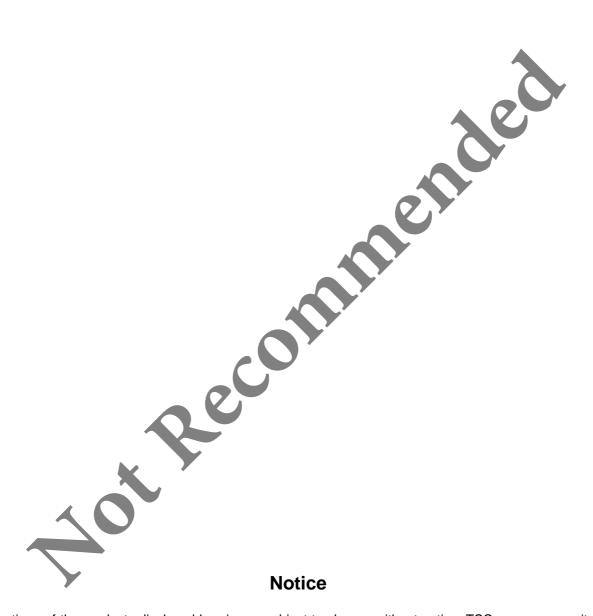
TSC

4N90 **GYWWF** 

# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







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